

**TOSHIBA FIELD EFFECT TRANSISTOR**  
**SILICON P CHANNEL MOS TYPE**

**2SJ115**

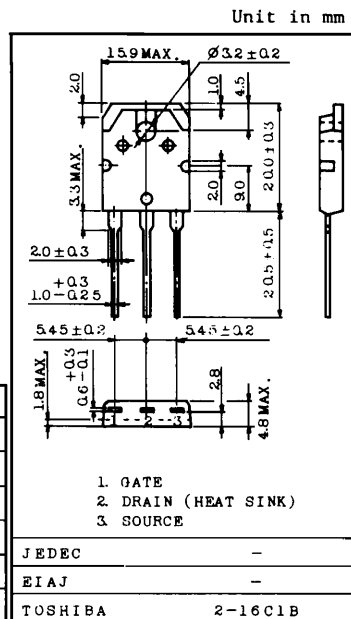
AUDIO FREQUENCY POWER AMPLIFIER APPLICATION.

FEATURES:

- High Breakdown Voltage :  $V_{DSS} = -160V$
- High Forward Transfer Admittance :  $|Y_{fs}| = 2.0S$  (Typ.)
- Complementary to 2SK405

MAXIMUM RATINGS ( $T_a = 25^\circ C$ )

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	$V_{DSS}$	-160	V
Gate-Source Voltage	$V_{GSS}$	$\pm 20$	V
Drain Current	$I_D$	-8	A
Power Dissipation ( $T_c = 25^\circ C$ )	$P_D$	100	W
Channel Temperature	$T_{ch}$	150	$^\circ C$
Storage Temperature Range	$T_{stg}$	-55 ~ 150	$^\circ C$



Weight : 4.6g

ELECTRICAL CHARACTERISTICS ( $T_a = 25^\circ C$ )

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current	$I_{GSS}$	$V_{DS} = 0, V_{GS} = \pm 20V$	-	-	$\pm 1.0$	$\mu A$
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = -5mA, V_{GS} = 0$	-160	-	-	V
Gate-Source Cut-off Voltage	$V_{GS(OFF)}$ (Note)	$V_{DS} = -10V, I_D = -0.1A$	-0.8	-	-2.8	V
Drain-Source Saturation Voltage	$V_{DS(ON)}$	$I_D = -5A, V_{GS} = -10V$	-	-3.5	-7.0	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = -10V, I_D = -2A$	1.0	2.0	-	S
Input Capacitance	$C_{iss}$	$V_{DS} = -10V, V_{GS} = 0, f = 1MHz$	-	800	-	pF
Output Capacitance	$C_{oss}$	$V_{DS} = -10V, V_{GS} = 0, f = 1MHz$	-	500	-	pF
Reverse Transfer Capacitance	$C_{rs}$	$V_{DS} = -10V, V_{GS} = 0, f = 1MHz$	-	110	-	pF

Note :  $V_{GS(OFF)}$  Classification 0 : -0.8 ~ -1.6, Y : -1.4 ~ -2.8

